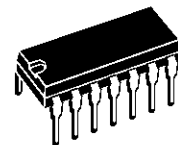
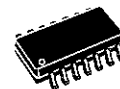


WIDE BANDWIDTH QUAD J-FET OPERATIONAL AMPLIFIERS

- LOW POWER CONSUMPTION
- WIDE COMMON-MODE (UP TO V_{CC}^+) AND DIFFERENTIAL VOLTAGE RANGE
- LOW INPUT BIAS AND OFFSET CURRENT
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT STAGE
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE : $16V/\mu s$ (typ)



N
DIP14
(Plastic Package)



D
SO14
(Plastic Micropackage)

DESCRIPTION

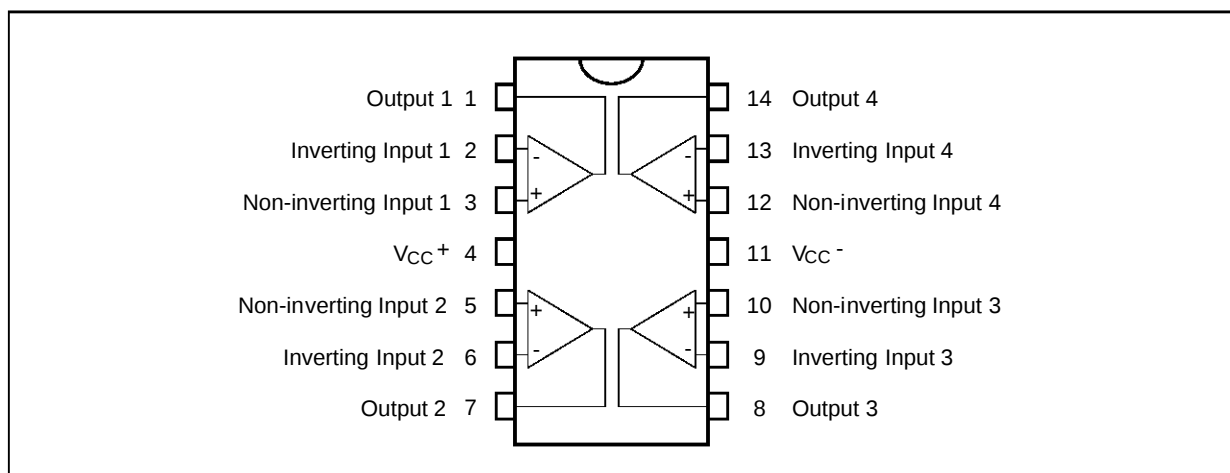
These circuits are high speed J-FET input quad operational amplifiers incorporating well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

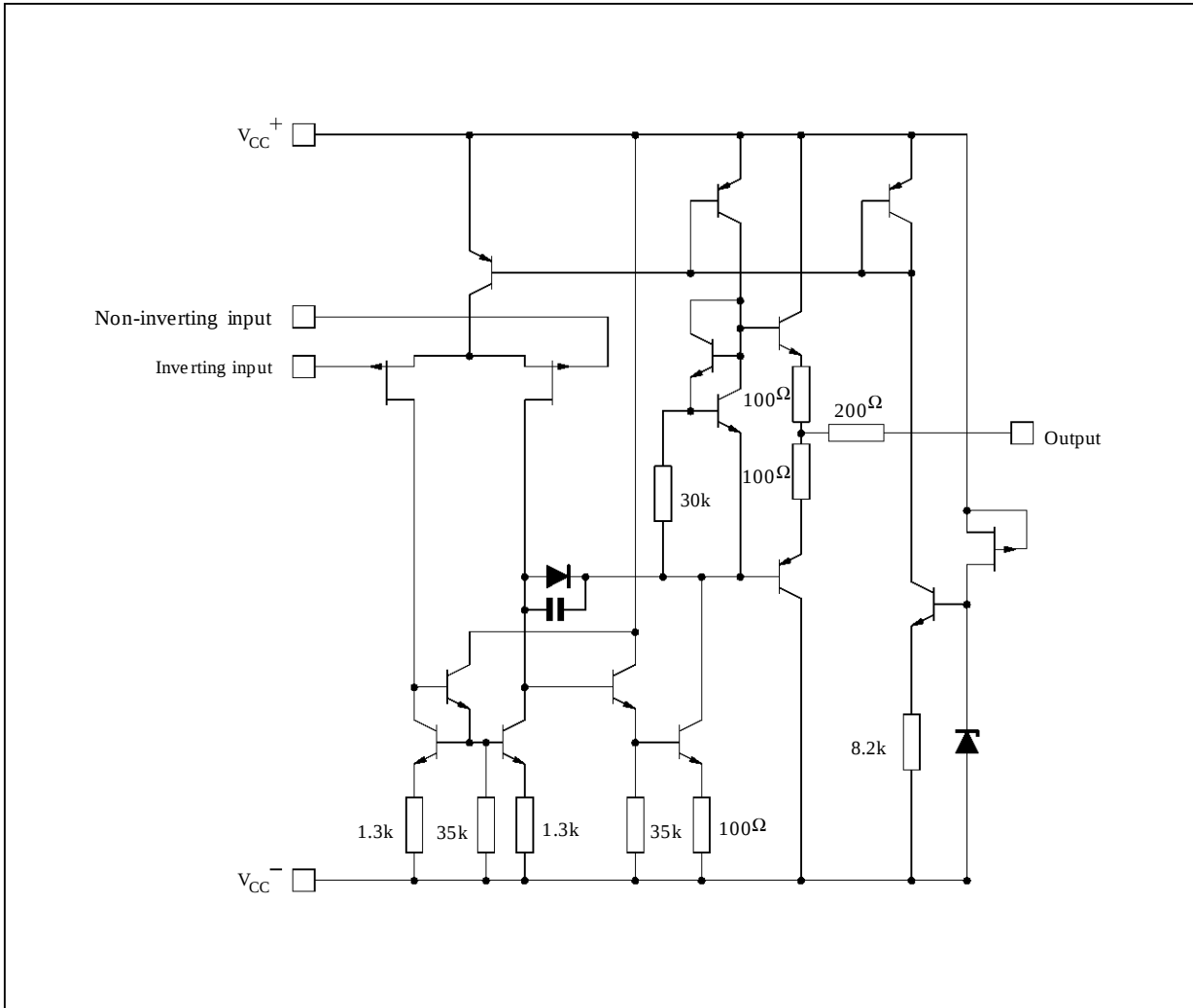
ORDER CODES

Part Number	Temperature Range	Package	
		N	D
LF347	0°C, +70°C	•	•
LF247	-40°C, +105°C	•	•
LF147	-55°C, +125°C	•	•
Example : LF347IN			

PIN CONNECTIONS (top view)



SCHEMATIC DIAGRAM (each amplifier)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage - (note 1)	±18	V
V _i	Input Voltage - (note 3)	±15	V
V _{id}	Differential Input Voltage - (note 2)	±30	V
P _{tot}	Power Dissipation	680	mW
	Output Short-circuit Duration - (note 4)	Infinite	
T _{oper}	Operating Free Air Temperature Range	LF347 -40 to 105 LF247 -55 to 125 LF147	°C
T _{stg}	Storage Temperature Range	-65 to 150	°C

- Notes :
1. All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between V_{CC}⁺ and V_{CC}⁻.
 2. Differential voltages are at the non-inverting input terminal with respect to the inverting input terminal.
 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less.
 4. The output may be shorted to ground or to either supply. Temperature and /or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

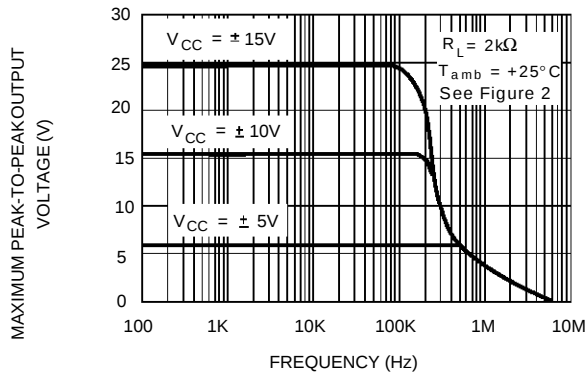
ELECTRICAL CHARACTERISTICS

$V_{CC} = \pm 15V$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

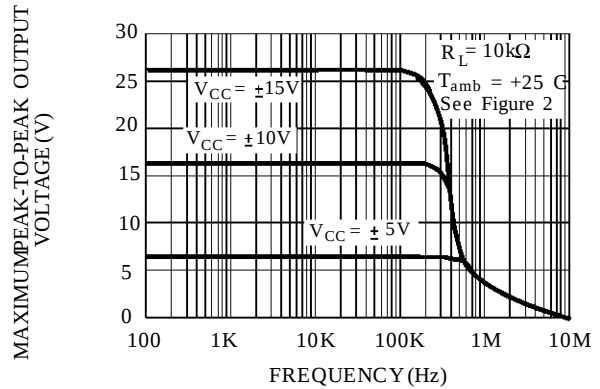
Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{io}	Input Offset Voltage ($R_S = 10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		3	10 13	mV
DV_{io}	Input Offset Voltage Drift		10		$\mu V/^{\circ}C$
I_{io}	Input Offset Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		5	100 4	pA nA
I_{ib}	Input Bias Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		20	200 20	pA nA
A_{vd}	Large Signal Voltage Gain ($R_L = 2k\Omega$, $V_O = \pm 10V$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	50 25	200		V/mV
SVR	Supply Voltage Rejection Ratio ($R_S = 10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	80 80	86		dB
I_{CC}	Supply Current, per Amp, no Load $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		1.4	2.7 2.7	mA
V_{icm}	Input Common Mode Voltage Range	± 11	+15 -12		V
CMR	Common Mode Rejection Ratio ($R_S = 10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	70 70	86		dB
I_{os}	Output Short-circuit Current $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$	10 10	40	60 60	mA
$\pm V_{OPP}$	Output Voltage Swing $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$ $R_L = 2k\Omega$ $R_L = 10k\Omega$ $R_L = 2k\Omega$ $R_L = 10k\Omega$	10 12 10 12	12 13.5		V
SR	Slew Rate ($V_i = 10V$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)	12	16		V/ μs
t_r	Rise Time ($V_i = 20mV$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)		0.1		μs
K_{OV}	Overshoot ($V_i = 20mV$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, unity gain)		10		%
GBP	Gain Bandwidth Product ($f = 100kHz$, $T_{amb} = 25^{\circ}C$, $V_{in} = 10mV$, $R_L = 2k\Omega$, $C_L = 100pF$)	2.5	4		MHz
R_i	Input Resistance		10^{12}		Ω
THD	Total Harmonic Distortion ($f = 1kHz$, $A_v = 20dB$, $R_L = 2k\Omega$, $C_L = 100pF$, $T_{amb} = 25^{\circ}C$, $V_O = 2V_{PP}$)		0.01		%
e_n	Equivalent Input Noise Voltage ($f = 1kHz$, $R_S = 100\Omega$)		15		$\frac{nV}{\sqrt{Hz}}$
ϕ_m	Phase Margin		45		Degrees
V_{O1}/V_{O2}	Channel Separation ($A_v = 100$)		120		dB

* The input bias currents are junction leakage currents which approximately double for every $10^{\circ}C$ increase in the junction temperature.

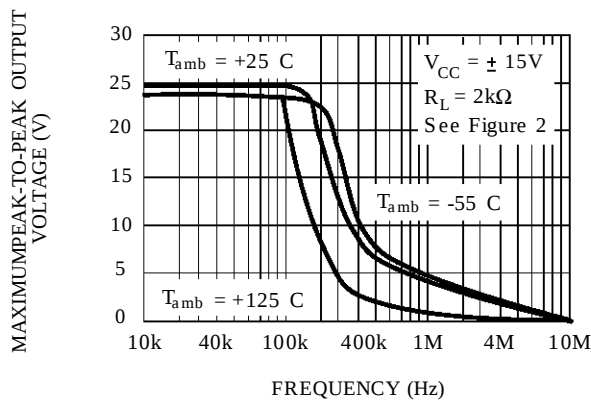
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



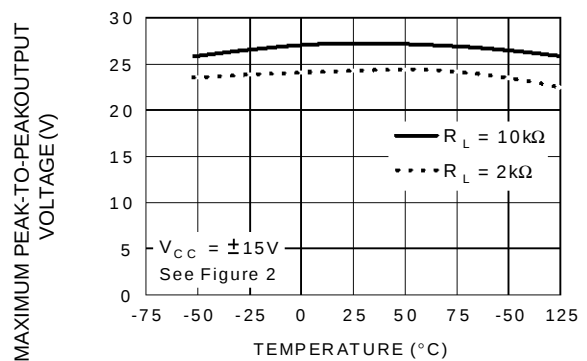
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



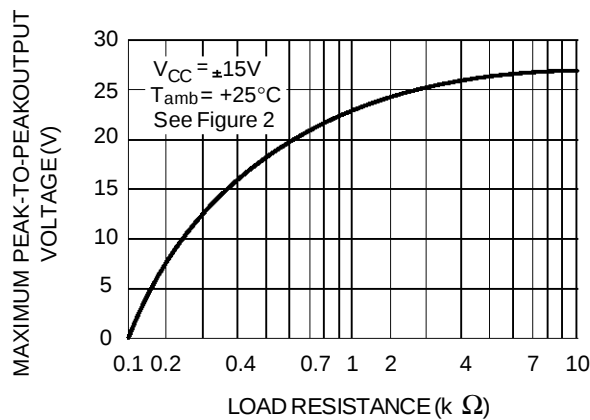
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



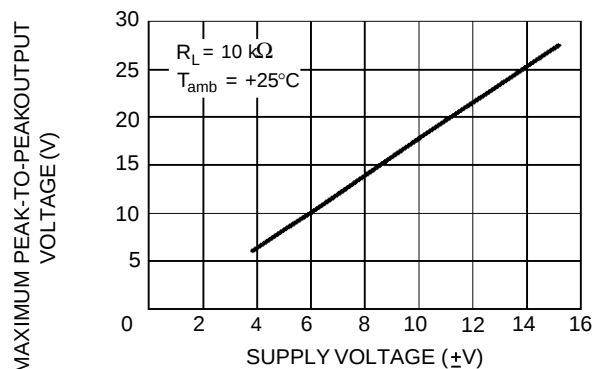
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREE AIR TEMP.



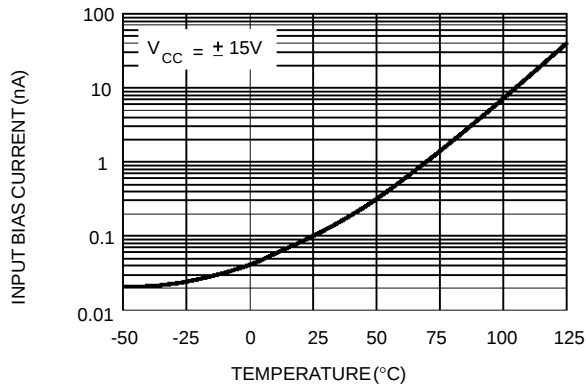
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS LOAD RESISTANCE



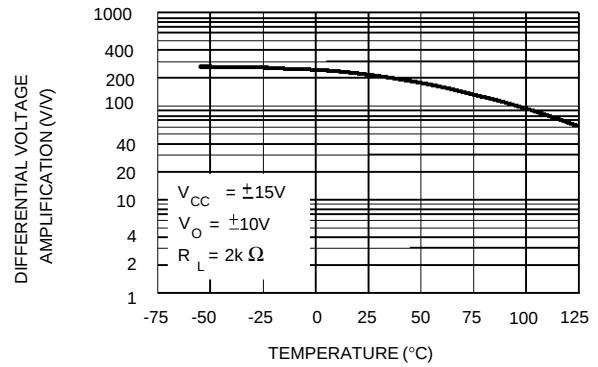
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS SUPPLY VOLTAGE



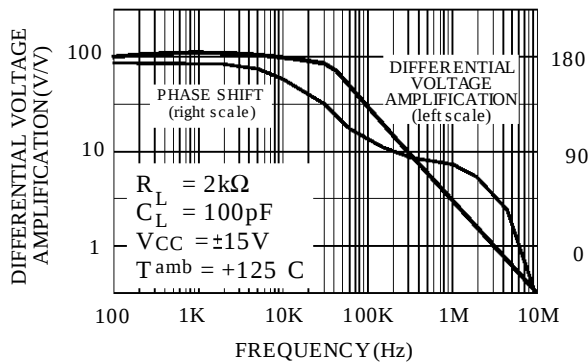
**INPUT BIAS CURRENT VERSUS
FREE AIR TEMPERATURE**



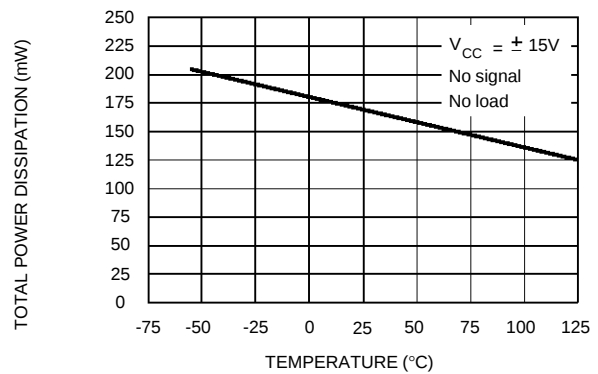
**LARGE SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION VERSUS
FREE AIR TEMPERATURE**



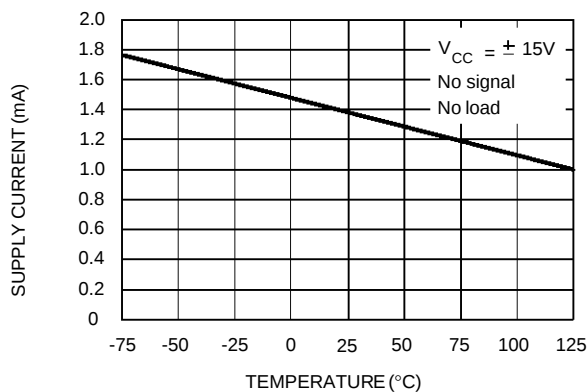
**LARGE SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION AND PHASE
SHIFT VERSUS FREQUENCY**



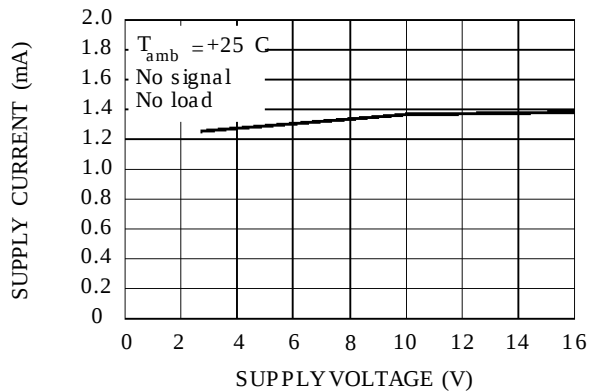
**TOTAL POWER DISSIPATION VERSUS
FREE AIR TEMPERATURE**



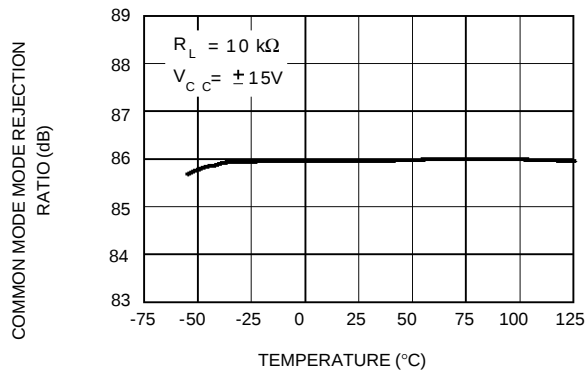
**SUPPLY CURRENT PER AMPLIFIER
VERSUS FREE AIR TEMPERATURE**



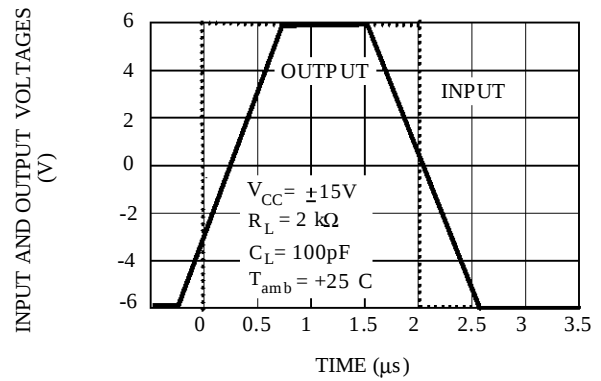
**COMMON MODE REJECTION RATIO
VERSUS FREE AIR TEMPERATURE**



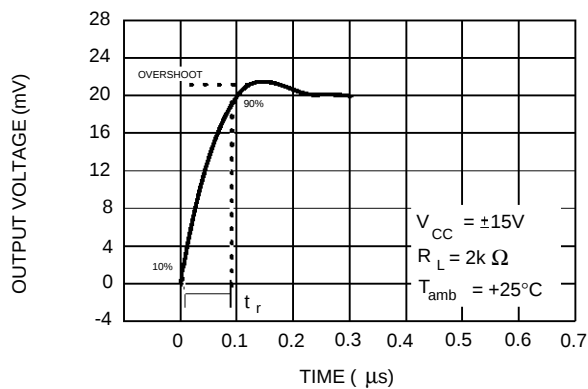
**COMMON MODE REJECTION RATIO
VERSUS FREE AIR TEMPERATURE**



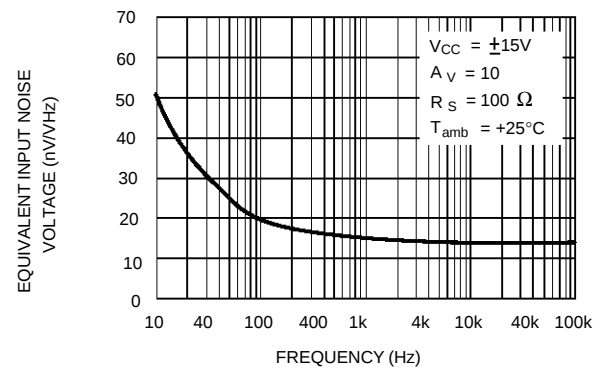
**VOLTAGE FOLLOWER LARGE SIGNAL
PULSE RESPONSE**



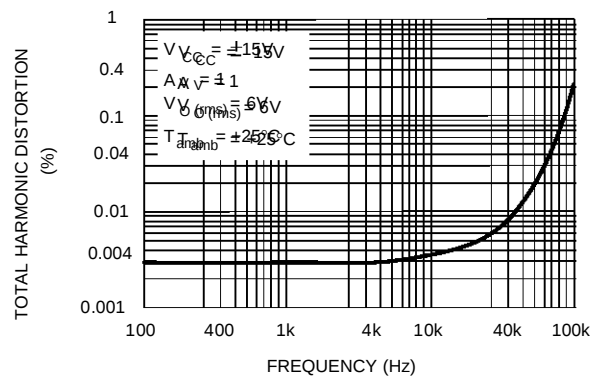
**OUTPUT VOLTAGE VERSUS
ELAPSED TIME**



**EQUIVALENT INPUT NOISE VOLTAGE
VERSUS FREQUENCY**



**TOTAL HARMONIC DISTORTION VERSUS
FREQUENCY**



PARAMETER MEASUREMENT INFORMATION

Figure 1 : Voltage Follower

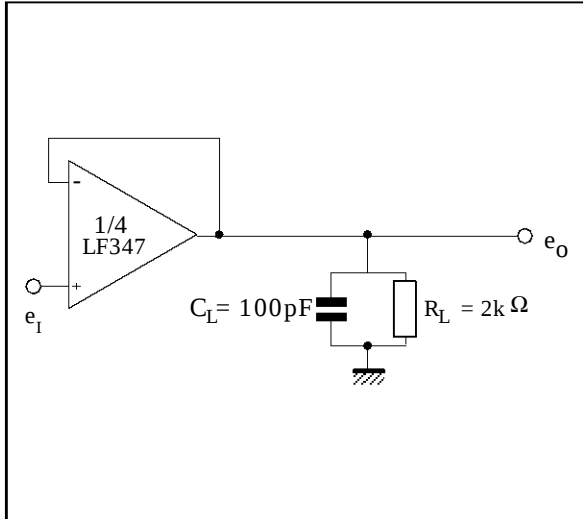
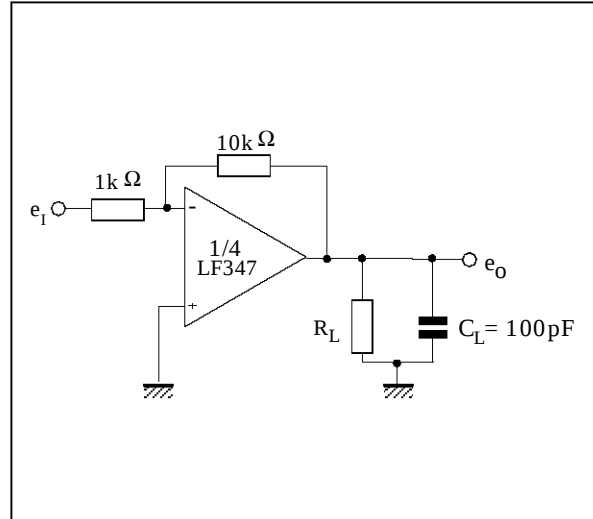
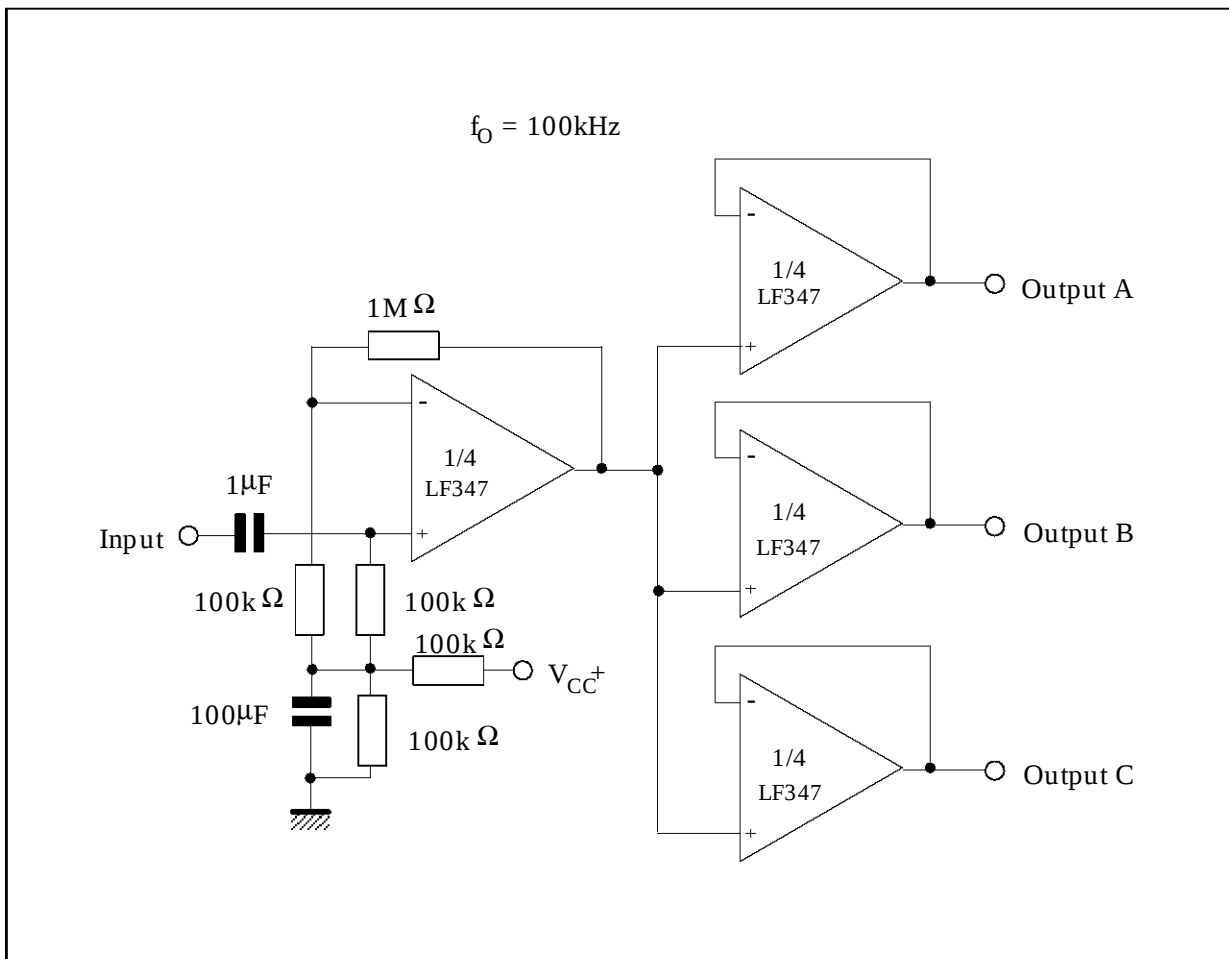


Figure 2 : Gain-of-10 Inverting Amplifier



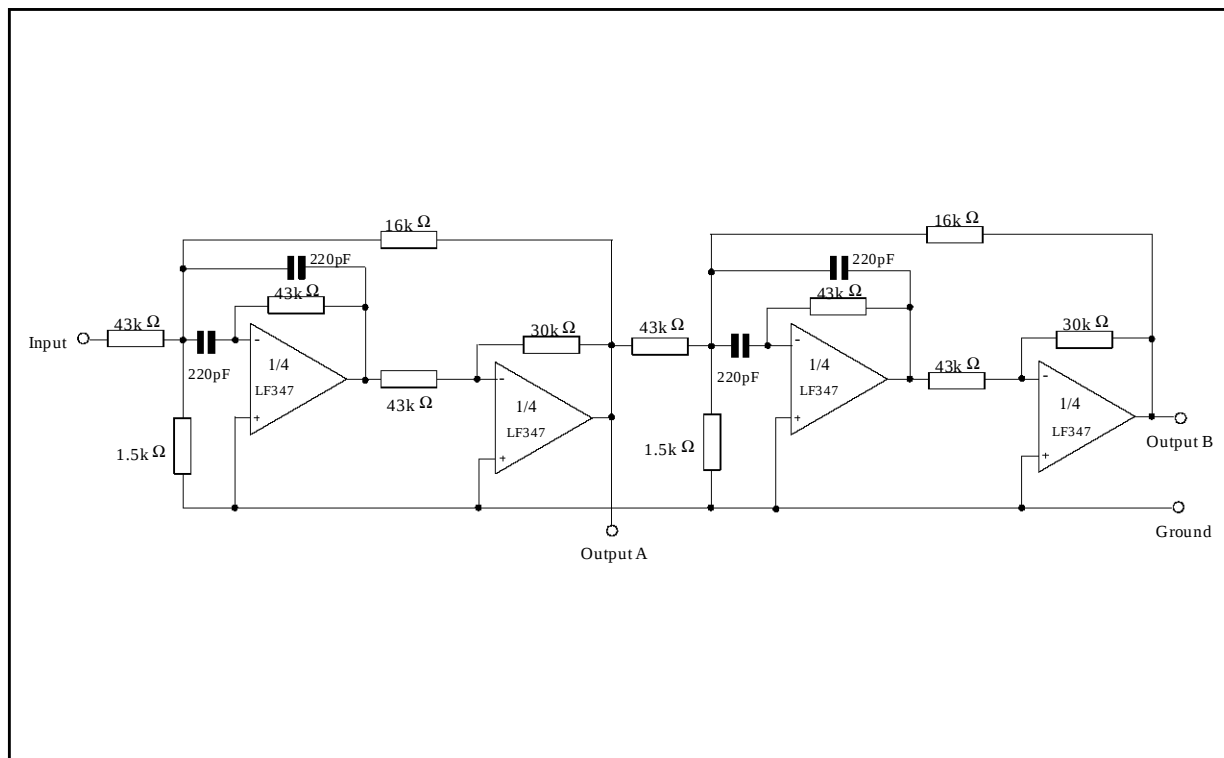
TYPICAL APPLICATIONS

AUDIO DISTRIBUTION AMPLIFIER

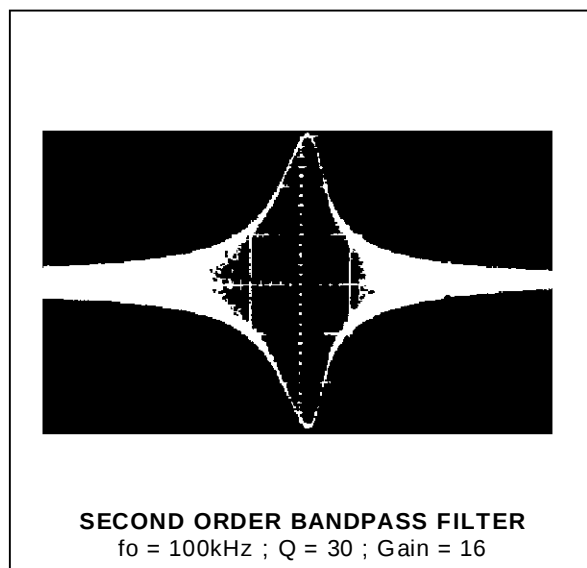


TYPICAL APPLICATIONS (continued)

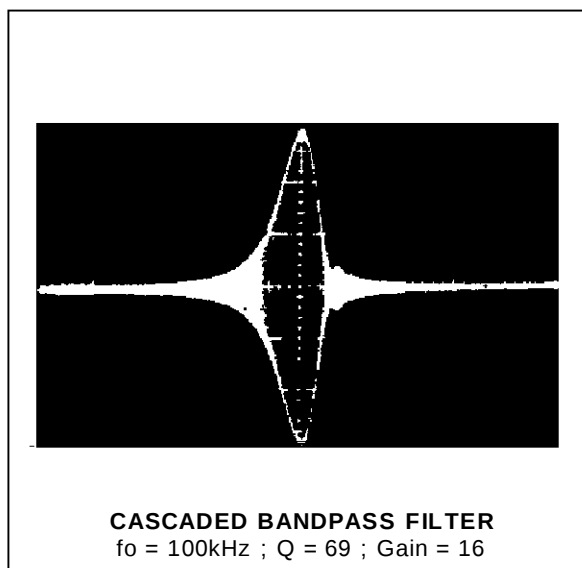
POSITIVE FEEDBACK BANDPASS FILTER



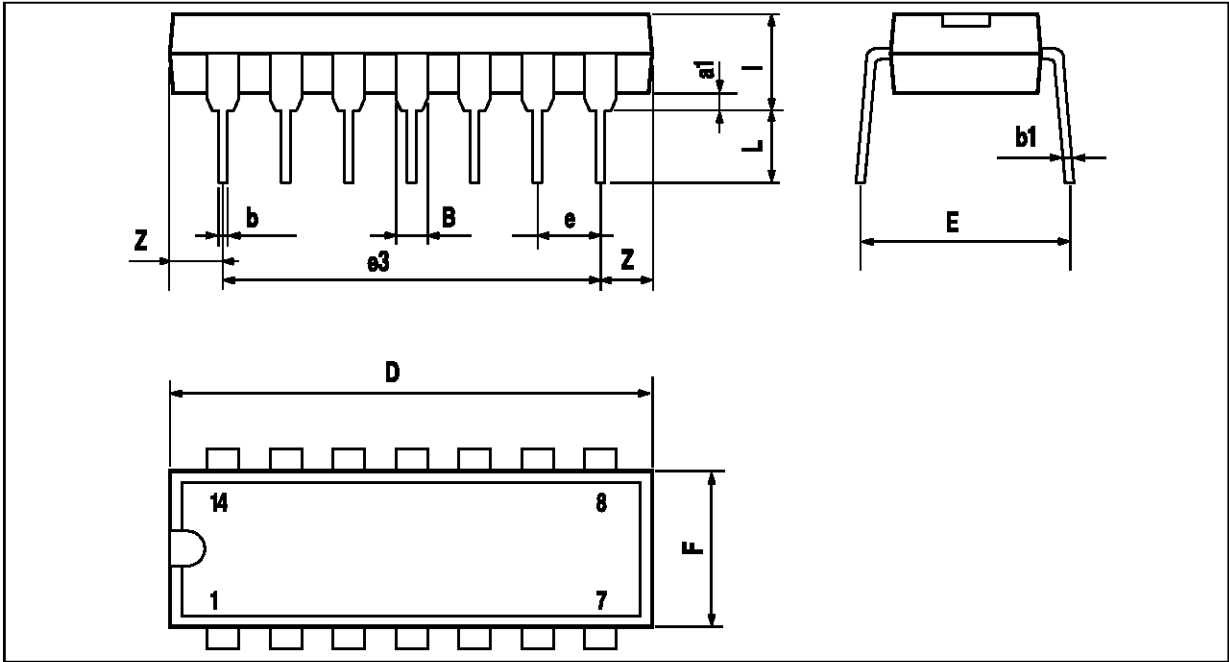
OUTPUT A



OUTPUT B



PACKAGE MECHANICAL DATA
14 PINS - PLASTIC DIP

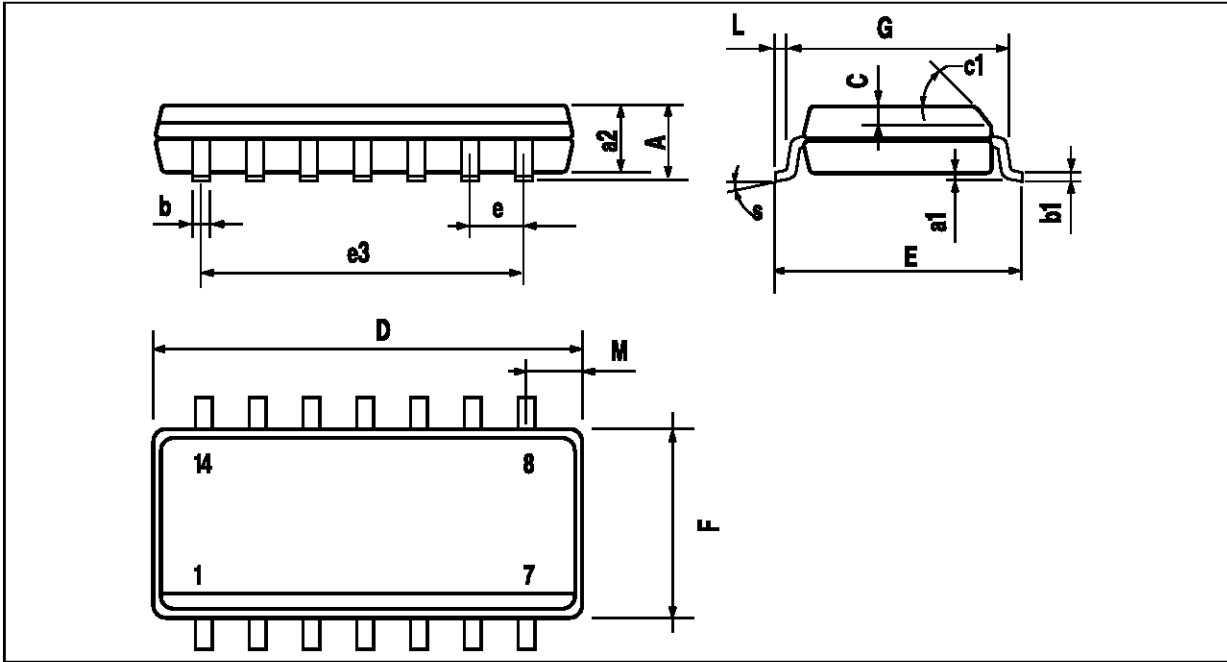


PM-DIP14.EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
i			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

DIP14.TBL

PACKAGE MECHANICAL DATA
14 PINS - PLASTIC MICROPACKAGE (SO)



Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.2	0.004		0.008
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.020	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.334
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.150		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.020		0.050
M			0.68			0.027
S	8° (max.)					

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1997 SGS-THOMSON Microelectronics – Printed in Italy – All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco
The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.